



P-Channel 40-V (D-S) MOSFET

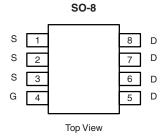
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
- 40	$0.014 \text{ at V}_{GS} = -10 \text{ V}$	- 10.5	40		
	0.021 at V _{GS} = - 4.5 V	- 8.7	40		

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

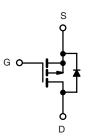






Ordering Information: Si4401BDY-T1-E3 (Lead (Pb)-free)

Si4401BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise i	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 40		
Gate-Source Voltage		V _{GS}	± 20		V
O D O (T 450.00)2	T _A = 25 °C	- I _D	- 10.5	- 8.7	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 8.3	- 5.9	
Pulsed Drain Current		I _{DM}	- 50		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.6	- 1.36	
Avalanche Current	L = 1 mH	I _{AS}		30	
Single Pulse Avalanche Energy	L=IIIII	E _{AS}		45	mJ
M ·	T _A = 25 °C	P _D	2.9	1.5	W
Maximum Power Dissipation ^a	T _A = 70 °C	1 ' ['] D	1.85	0.95	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55	to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manipulation to Applicate	t ≤ 10 s	R _{thJA}	B	43	°C/W
Maximum Junction-to-Ambient ^a	Steady State	' ¹ thJA	70	84	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	16	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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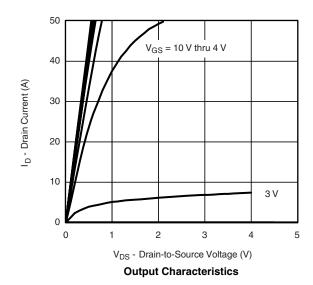
SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Coto Valtono Duoin Comunit		V _{DS} = - 40 V, V _{GS} = 0 V		- 1			
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			- 10	μΑ	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 30			Α	
Durin Course On Obela Desirtance	B	V _{GS} = - 10 V, I _D = - 10.5 A		0.011	0.014	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 8.7 A		0.0165	0.021	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 10.5 A		26		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 2.7 A, V _{GS} = 0 V		- 0.74	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Q_g			40	55		
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -5 \text{ V}, I_D = -10.5 \text{ A}$		10		nC	
Gate-Drain Charge	Q_{gd}			14			
Gate Resistance	R_g		1.4	2.8	4.2	Ω	
Turn-On Delay Time	t _{d(on)}			16	25		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		15	25		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, $V_{GEN} =$ - 10 V, $R_g = 6 \Omega$		97	150	ns	
Fall Time	t _f			47	75		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.1 A, dI/dt = 100 A/μs		35	55		

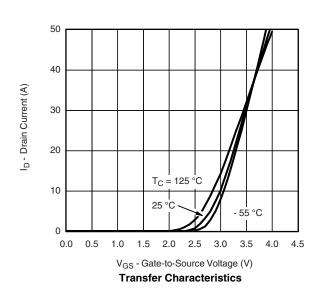
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



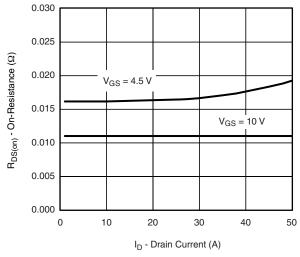




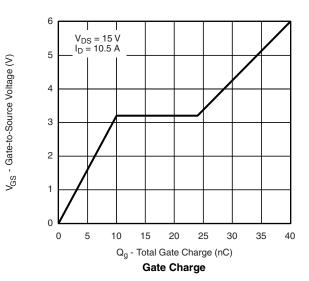


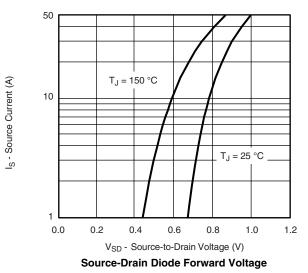


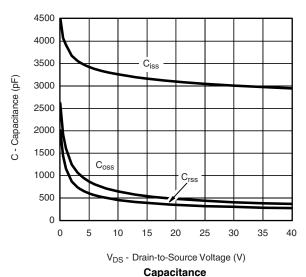
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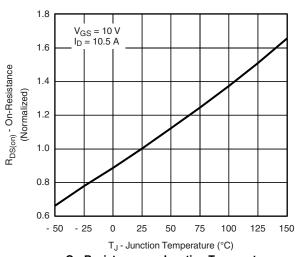


On-Resistance vs. Drain Current

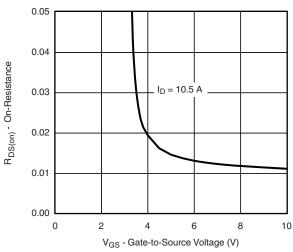








On-Resistance vs. Junction Temperature

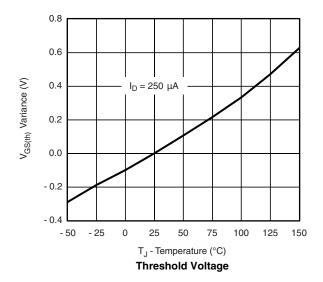


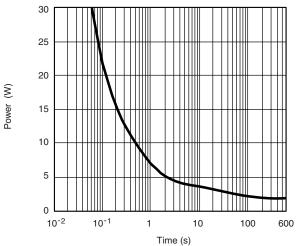
On-Resistance vs. Gate-to-Source Voltage

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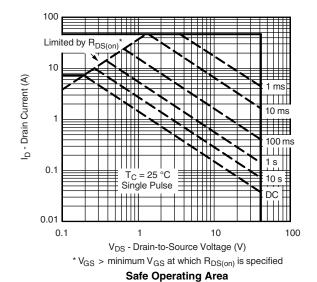
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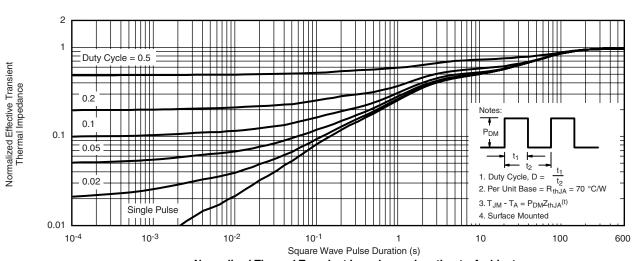
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Single Pulse Power, Junction-to-Ambient

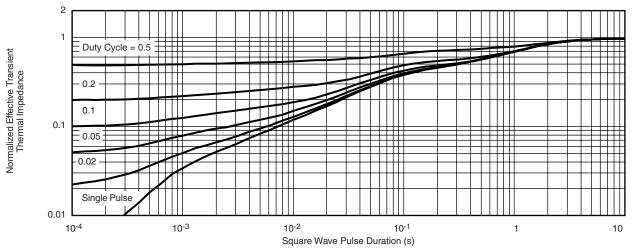




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIMETERS INCHES			HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27 BSC		0.050	50 BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

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